

SILICON EPITAXIAL PLANAR DIODE

Band Switching Diode

Features

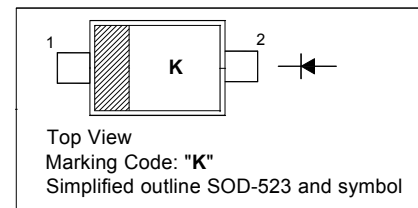
- Extremely small surface mounting type
- High reliability

Applications

- High frequency switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 25\text{ V}$	I_R	10	nA
Capacitance Between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_T	1.2	pF
Forward Operating Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$	r_f	0.9	Ω

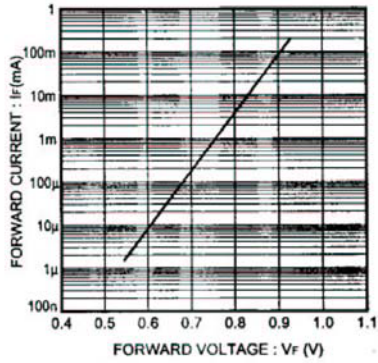


Fig. 1 Forward characteristics

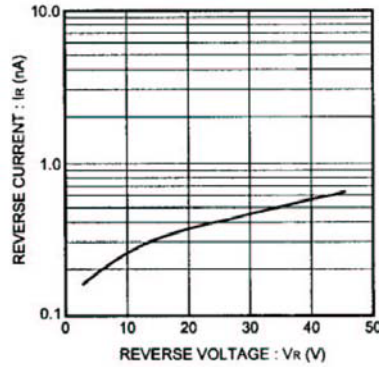


Fig. 2 Reverse characteristics

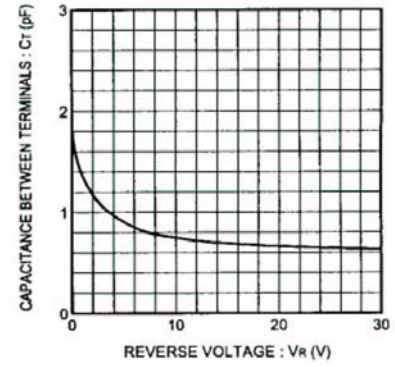


Fig. 3 Capacitance between terminals characteristics

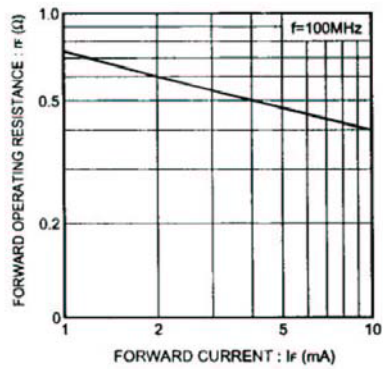


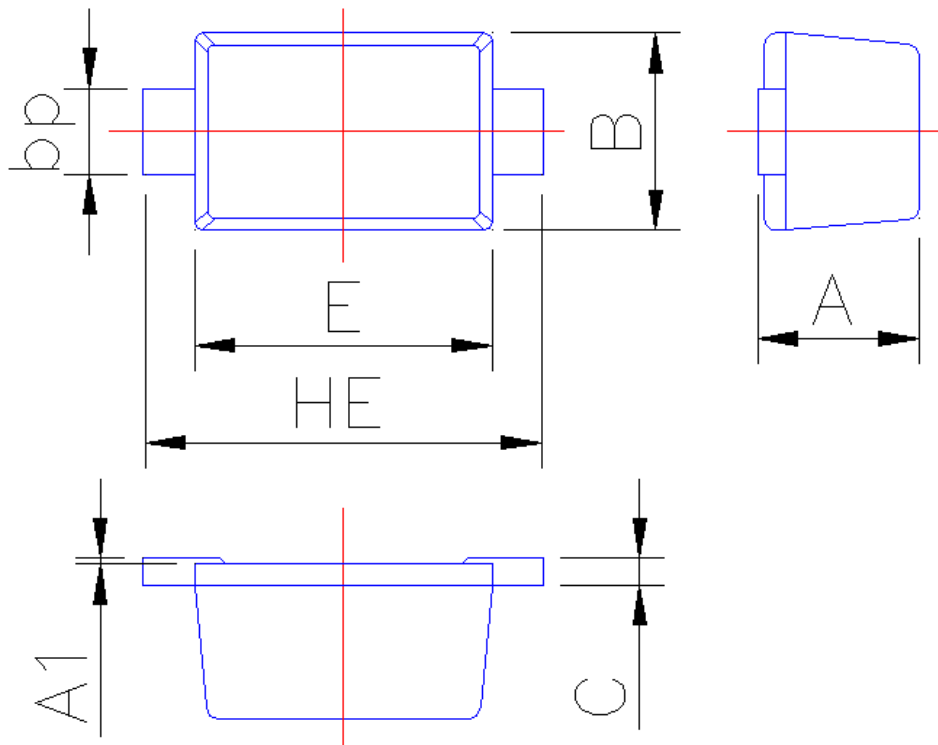
Fig. 4 Forward operating resistance characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70